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Effects of Substrate Temperature on Properties of a-SiN_x:H Films

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Abstract: Hydrogenated amorphous silicon nitride films were prepared in an rf glow-discharge system by the decomposition of silane + nitrogen gas mixture at various substrate temperatures. The effects of substrate temperature on the electrical and optical properties of the films have been studied.

Key Words: A. Hydrogenated amorphous silicon nitride; B. Substrate temperature; C. Dark conductivity; D. Photoconductivity; E. Optical gap.

 [Keywords](#)
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